Features

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable rectifiers
- Controlled rectifiers

$I_{F(AV)}$ 1080A
V_{RRM} 1100 ～ 2000V
I_{FSM} 10 kA
I^2t 500 10^3A^2S

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T_j(°C)	VALUE			UNIT
					Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Double side cooled,	T_C=85°C	175			1080	A
V_{RRM}	Repetitive peak reverse voltage	tp=10ms		175	1100		2000	V
I_{RRM}	Repetitive peak current	at V_{RRM}		175			30	mA
I_{FSM}	Surge forward current	10ms half sine wave V_R=0.6V_{RRM}		175			10	kA
I^2t	I^2t for fusing coordination						500	A^2s*10^3
V_{FO}	Threshold voltage			175			0.98	V
r_F	Forward slope resistance						0.33	mΩ
V_{FM}	Peak forward voltage	I_{FM}=1200A, F=7.0kN		25			1.80	V
Q_{rr}	Recovery charge	I_{FM}=1000A, tp=4000μs, di/dt=-20A/μs, V_R=100V		175		1600		μC
$R_{th(j-c)}$	Thermal resistance Junction to case	D.C. double side cooled Clamping force 7.0kN					0.045	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink						0.010	
F_m	Mounting force				5.3		10	kN
T_{vj}	Junction temperature				-40		175	°C
T_{stg}	Stored temperature				-40		175	°C
W_t	Weight					80		g
Outline	P33							

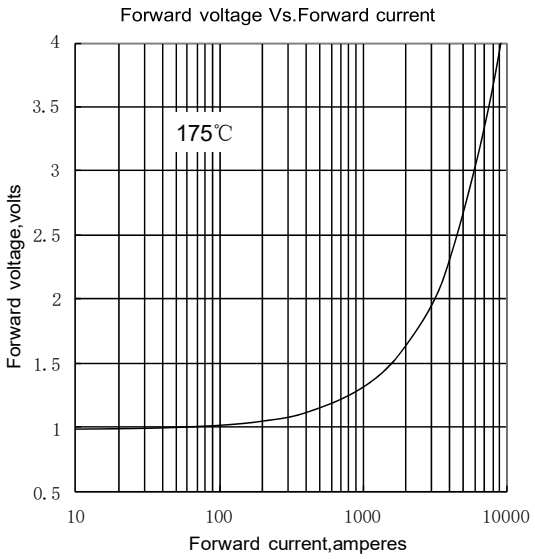

Fig.1

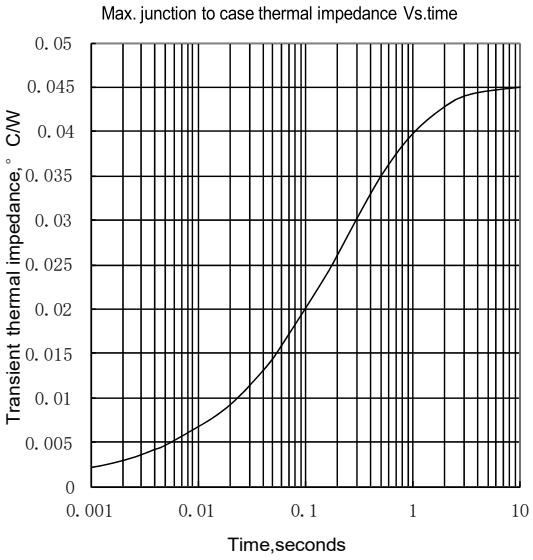

Fig.2

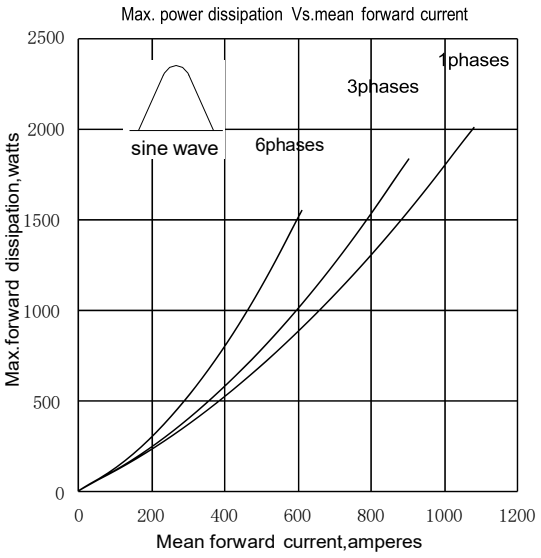

Fig.3

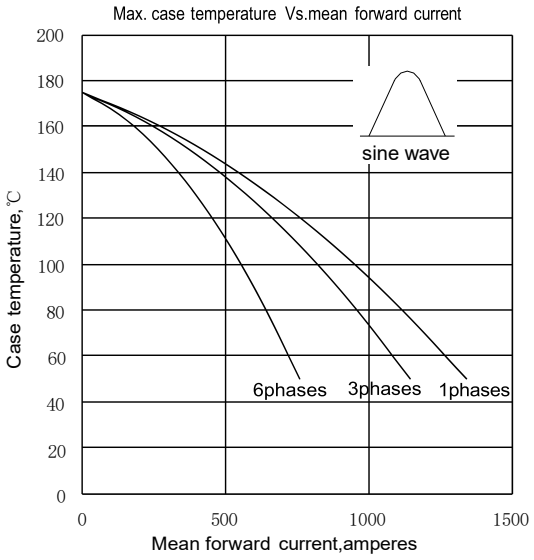

Fig.4

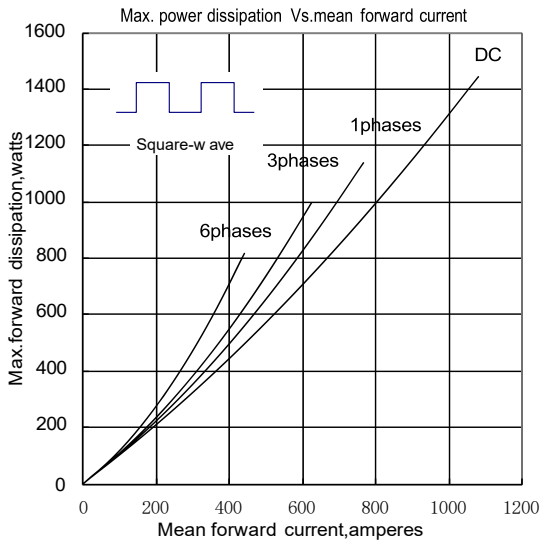

Fig.5

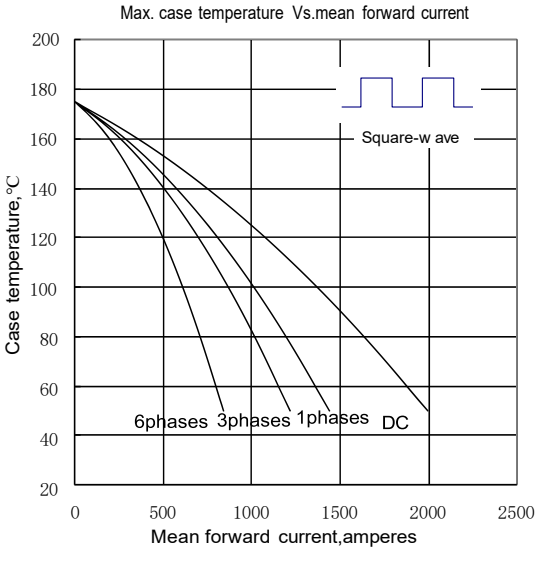

Fig.6

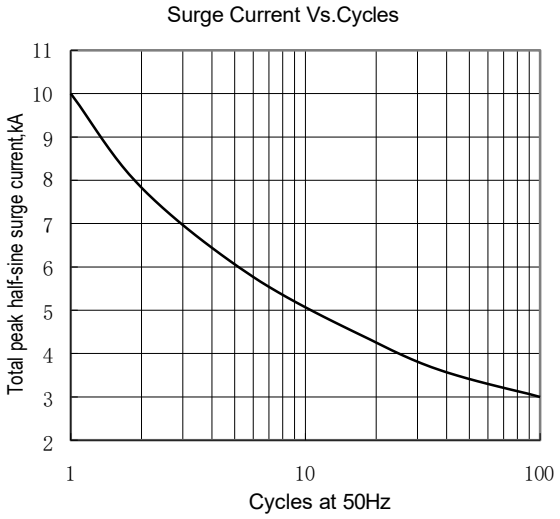

Fig.7

Outline: